# NPN SILICON RF POWER TRANSISTOR

## DESCRIPTION:

The **ASI BLV20** is Designed for Class C, 28 V High Band Applications up to 175 MHz.

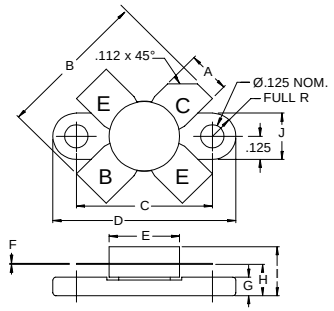
## FEATURES:

- Common Emitter
- $P_G$ = 12 dB at 8.0 W/175 MHz
- ***Omnigold***™ Metalization System

## MAXIMUM RATINGS

| | |
|---|---|
| $I_C$ | 1.0 A |
| $V_{CBO}$ | 65 V |
| $V_{CEO}$ | 35 V |
| $V_{CES}$ | 65 V |
| $V_{EBO}$ | 4.0 V |
| $P_{DISS}$ | 20 W @ $T_C$ = 25 ° C |
| $T_J$ | -65 °C to +200 °C |
| $T_{STG}$ | -65 °C to +150°C |
| $\theta_{JC}$ | 8.75 °C/W |

## PACKAGE STYLE .380 4L FLG




| DIM | MINIMUM inches / mm | MAXIMUM inches / mm |
|---|---|---|
| A | .220 / 5.59 | .230 / 5.84 |
| B | .785 / 19.94 | |
| C | .720 / 18.29 | .730 / 18.54 |
| D | .970 / 24.64 | .980 / 24.89 |
| E | | .385 / 9.78 |
| F | .004 / 0.10 | .006 / 0.15 |
| G | .085 / 2.16 | .105 / 2.67 |
| H | .160 / 4.06 | .180 / 4.57 |
| I | | .280 / 7.11 |
| J | .240 / 6.10 | .255 / 6.48 |

## CHARACTERISTICS $T_C$ = 25 °C

| SYMBOL | TEST CONDITIONS | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|---|---|---|---|---|---|
| $BV_{CBO}$ | $I_C$ = 200 mA | 65 | | | V |
| $BV_{CES}$ | $I_C$ = 2.0 mA | 65 | | | V |
| $BV_{CEO}$ | $I_C$ = 10 mA | 35 | | | V |
| $BV_{EBO}$ | $I_E$ = 1.0 mA | 4.0 | | | V |
| $I_{CBO}$ | $V_{CB}$ = 36 V | | | 1.0 | mA |
| $h_{FE}$ | $V_{CE}$ = 5.0 V $I_C$ = 400 mA | 10 | | 100 | --- |
| $C_C$ | $V_{CB}$ = 28 V f = 1.0 MHz | | 10 | | pF |
| $P_G$ | $V_{CC}$ = 28 V $P_{OUT}$ = 8.0 W f = 175 MHz | 12 | | | dB |
| $\eta_C$ | | | 60 | | % |



*Specifications are subject to change without notice.*